# **MMVL109T1**

Preferred Device

# **Silicon Epicap Diodes**

Designed for general frequency control and tuning applications; providing solid-state reliability in replacement of mechnaical tuning methods.

- High Q with Guaranteed Minimum Values at VHF Frequencies
- Controlled and Uniform Tuning Ratio
- Surface Mount Package
- Device Marking: 4A



#### ON Semiconductor™

http://onsemi.com

## 26–32 pF VOLTAGE VARIABLE CAPACITANCE DIODES

#### **MAXIMUM RATINGS**

Symbol	Rating	Value	Unit
٧R	Continuous Reverse Voltage	30	Vdc
ΙF	Peak Forward Current	200	mAdc

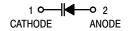
#### THERMAL CHARACTERISTICS

Symbol	Characteristic	Max	Unit
PD	Total Device Dissipation FR-5 Board,*  T <sub>A</sub> = 25°C  Derate above 25°C	200 1.57	mW mW/°C
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	635	°C/W
T <sub>J</sub> , T <sub>stg</sub>	Junction and Storage Temperature Range	-55 to +150	°C

\*FR-5 Minimum Pad



PLASTIC SOD-323 CASE 477



#### **ORDERING INFORMATION**

Device	Package	Shipping		
MMVL109T1	SOD-323	3000 / Tape & Reel		

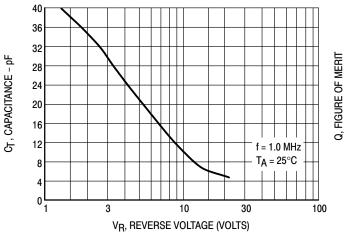
**Preferred** devices are recommended choices for future use and best overall value.

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Breakdown Voltage (I <sub>R</sub> = 10 μAdc)	V(BR)R	30	_	_	Vdc
Reverse Voltage Leakage Current (V <sub>R</sub> = 25 Vdc)	IR	_	_	0.1	μAdc
Diode Capacitance Temperature Coefficient (V <sub>R</sub> = 3.0 Vdc, f = 1.0 MHz)	TCC	_	300	_	ppm/°C

	C <sub>t</sub> , Diode Capacitance V <sub>R</sub> = 3.0 Vdc, f = 1.0 MHz pF		Q, Figure of Merit V <sub>R</sub> = 3.0 Vdc f = 50 MHz	C <sub>R</sub> , Capacitance Ratio C <sub>3</sub> /C <sub>25</sub> f = 1.0 MHz (Note 1)		
Device	Min	Nom	Max	Min	Min	Max
MMVL109T1	26	29	32	200	5.0	6.5

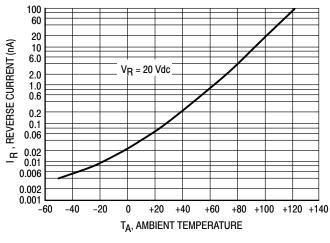
<sup>1.</sup>  $C_R$  is the ratio of  $C_t$  measured at 3 Vdc divided by  $C_t$  measured at 25 Vdc.



1000 V<sub>R</sub> = 3 Vdc T<sub>A</sub> = 25°C

Figure 1. DIODE CAPACITANCE

Figure 2. FIGURE OF MERIT



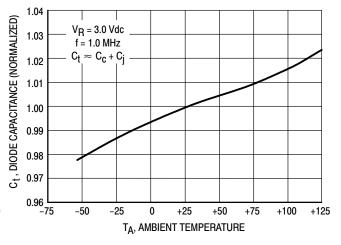


Figure 3. LEAKAGE CURRENT

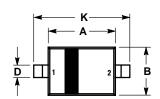
Figure 4. DIODE CAPACITANCE

#### NOTES ON TESTING AND SPECIFICATIONS

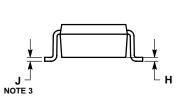
1.  $C_R$  is the ratio of  $C_t$  measured at 3.0 Vdc divided by  $C_t$  measured at 25 Vdc.

### **MMVL109T1**

#### **PACKAGE DIMENSIONS**



SOD-323 PLASTIC PACKAGE CASE 477-02 **ISSUE A** 





- NOTES:

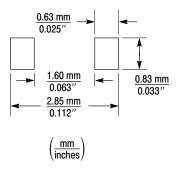
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETERS.

  3. LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	1.60	1.80	0.063	0.071	
В	1.15	1.35	0.045	0.053	
С	0.80	1.00	0.031	0.039	
D	0.25	0.40	0.010	0.016	
Е	0.15 REF		0.006 REF		
Н	0.00	0.10	0.000	0.004	
J	0.089	0.177	0.0035	0.0070	
K	2.30	2.70	0.091	0.106	

STYLE 1: PIN 1. CATHODE 2. ANODE



SOD-323 Soldering Footprint

#### **MMVL109T1**

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